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45.

A semiconductor device comprising:
a bulk semiconductor region; and
a semiconductor-on-insulator region comprising:
a crystallized semiconductor layer formed by annealing amorphous
semiconductor and having isolation trenches formed therein so as to remove defective
regions, and
isolation oxides formed in said isolation trenches. - -

IN THE ABSTRACT:

Please replace the Abstract as follows:

- - A semiconductor device includes a combination substrate having a bulk silicon
region, and a silicon-on-insulator (SOI) region. The SOI region includes a crystallized silicon
layer formed by annealing amorphous silicon and having isolation trenches formed therein so
as to remove defective regions, and isolation oxides formed in the isolation trenches. - -